ON Semiconductor®

FDC638APZ

P-Channel 2.5V PowerTrench® Specified MOSFET

–20V, –4.5A, 43mΩ

Features

- Max $r_{DS(on)}$ = 43mΩ at V_{GS} = –4.5V, I_D = –4.5A
- Max $r_{DS(on)}$ = 68mΩ at V_{GS} = –2.5V, I_D = –3.8A
- Low gate charge (8nC typical).
- High performance trench technology for extremely low $r_{DS(on)}$.
- SuperSOT™ –6 package:small footprint (72% smaller than standard SO–8) low profile (1mm thick).
- RoHS Compliant

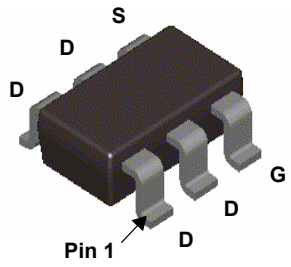
General Description

This P-Channel 2.5V specified MOSFET is produced using ON Semiconductor's advanced PowerTrench® process that has been especially tailored to minimize the on-state resistance and yet maintain low gate charge for superior switching performance

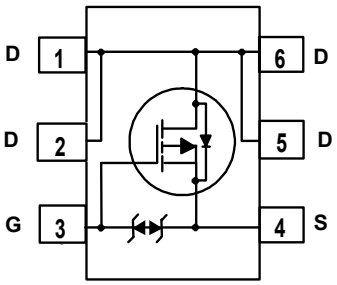
These devices are well suited for battery power applications:load switching and power management,battery charging circuits,and DC/DC conversion.

Application

- DC - DC Conversion



SuperSOT™ -6



MOSFET Maximum Ratings T_A= 25°C unless otherwise noted

Symbol	Parameter		Ratings	Units
V_{DS}	Drain to Source Voltage		–20	V
V_{GS}	Gate to Source Voltage		±12	V
I_D	Drain Current -Continuous	(Note 1a)	–4.5	A
	-Pulsed		–20	
P_D	Power Dissipation	(Note 1a)	1.6	W
	Power Dissipation	(Note 1b)	0.8	
T_J, T_{STG}	Operating and Storage Junction Temperature Range		–55 to +150	°C

Thermal Characteristics

$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	(Note 1a)	78	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	(Note 1b)	156	

Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape Width	Quantity
.638Z	FDC638APZ	7”	8mm	3000 units

Electrical Characteristics T_J = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Off Characteristics						
BV_{DSS}	Drain to Source Breakdown Voltage	I_D = –250μA, V_{GS} = 0V	–20			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	I_D = –250μA, referenced to 25°C		–9.4		mV/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = –16V, V_{GS} = 0V			–1	μA
		V_{GS} = 0V, T_J = 55°C			–10	
I_{GSS}	Gate to Source Leakage Current	V_{GS} = ±12V, V_{DS} = 0V			±10	μA
On Characteristics						
$V_{GS(th)}$	Gate to Source Threshold Voltage	V_{GS} = V_{DS}, I_D = –250μA	–0.4	–0.8	–1.5	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	I_D = –250μA, referenced to 25°C		2.9		mV/°C
$r_{DS(on)}$	Static Drain to Source On Resistance	V_{GS} = –4.5V, I_D = –4.5A		37	43	mΩ
		V_{GS} = –2.5V, I_D = –3.8A		52	68	
		V_{GS} = –4.5V, I_D = –4.5A, T_J = 125°C		50	72	
$I_{D(on)}$	On-State Drain Current	V_{GS} = –10V, V_{DS} = –4.5A	–20			A
g_{FS}	Forward Transconductance	V_{DS} = –10V, I_D = –4.5A		18		S
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS} = –10V, V_{GS} = 0V, f = 1MHz		750	1000	pF
C_{oss}	Output Capacitance			155	210	pF
C_{rss}	Reverse Transfer Capacitance			130	195	pF
Switching Characteristics (Note 2)						
$t_{d(on)}$	Turn-On Delay Time	V_{DD} = –5V, I_D = –4.5A, V_{GS} = –4.5V, R_{GEN} = 6Ω		6	12	ns
t_r	Rise Time			20	31	ns
$t_{d(off)}$	Turn-Off Delay Time			48	77	ns
t_f	Fall Time			47	72	ns
$Q_{g(TOT)}$	Total Gate Charge	V_{GS} = 0V to –4.5V, V_{DD} = –5V, I_D = –4.5A		8	12	nC
Q_{gs}	Gate to Source Gate Charge			2		nC
Q_{gd}	Gate to Drain “Miller” Charge			2		nC
Drain-Source Diode Characteristics						
I_S	Maximum Continuous Drain-Source Diode Forward Current				–1.3	A
V_{SD}	Source to Drain Diode Forward Voltage	V_{GS} = 0V, I_S = –1.3A (Note 2)		–0.8	–1.2	V
t_{rr}	Reverse Recovery Time	I_F = –4.5A, di/dt = 100A/μs		24	36	ns
Q_{rr}	Reverse Recovery Charge			13	20	nC

Notes:

1: $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by user's board design.

a. 78°C/W when mounted on a 1 in^2 pad of 2 oz copper on FR-4 board.

b. 156°C/W when mounted on a minimum pad of 2 oz copper.

2: Pulse Test: Pulse Width < 300μs, Duty cycle < 2.0%.

Typical Characteristics T_J = 25°C unless otherwise noted

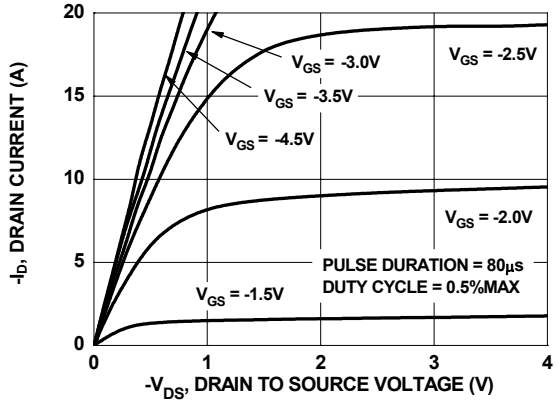


Figure 1. On-Region Characteristics

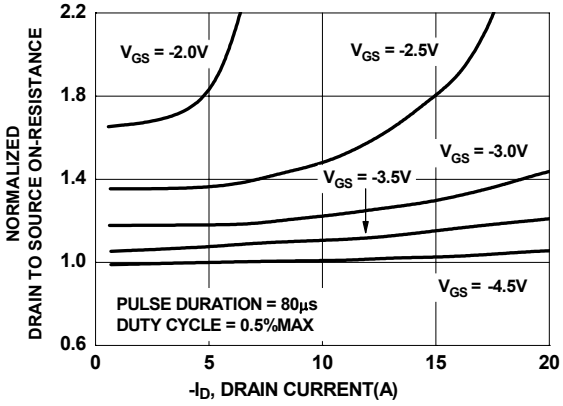


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

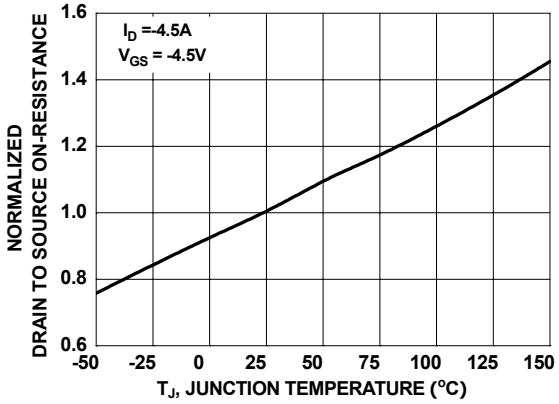


Figure 3. Normalized On-Resistance vs Junction Temperature

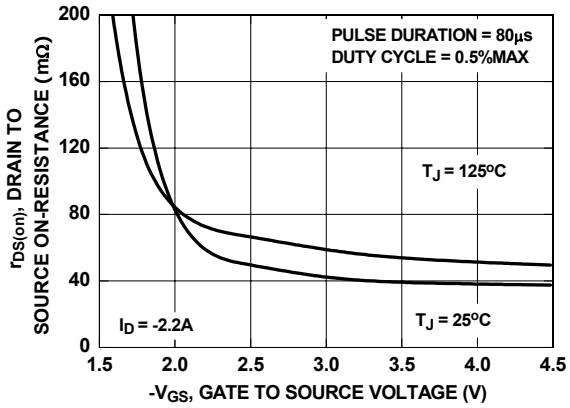


Figure 4. On-Resistance vs Gate to Source Voltage

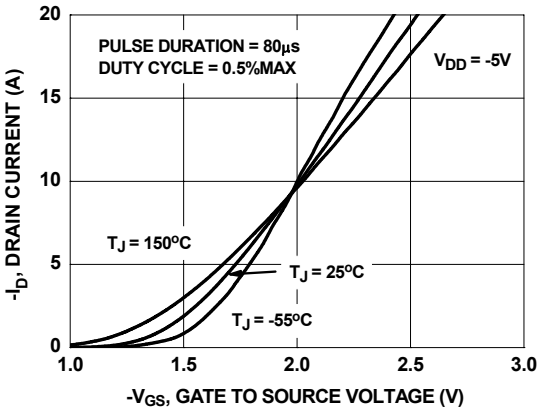


Figure 5. Transfer Characteristics

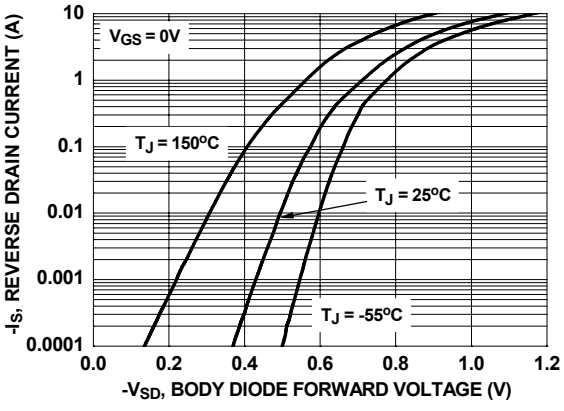


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

Typical Characteristics T_J = 25°C unless otherwise noted

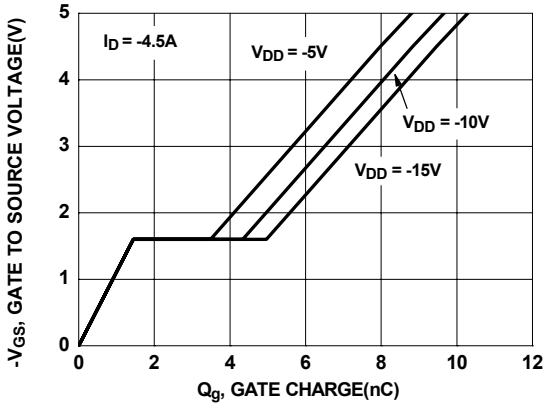


Figure 7. Gate Charge Characteristics

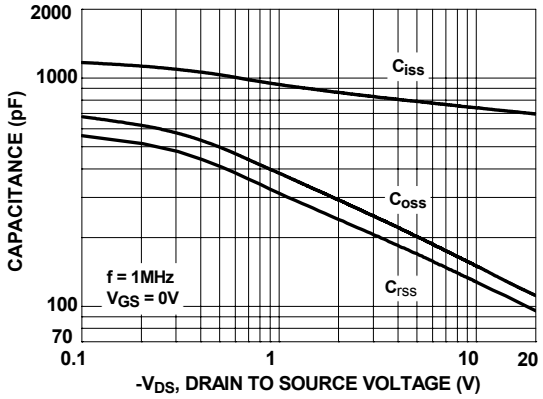


Figure 8. Capacitance vs Drain to Source Voltage

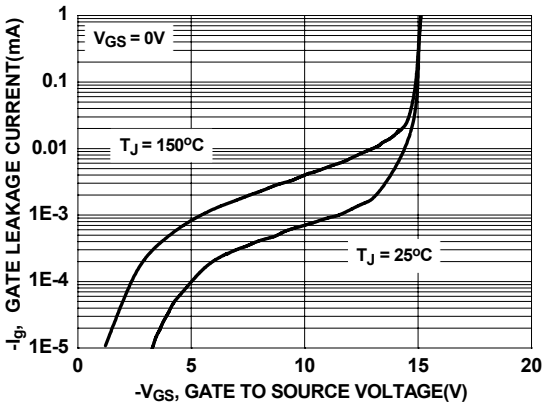


Figure 9. Gate Leakage Current vs Gate to Source Voltage

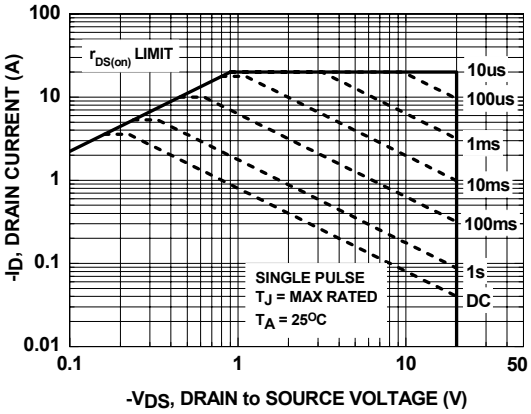


Figure 10. Forward Bias Safe Operating Area

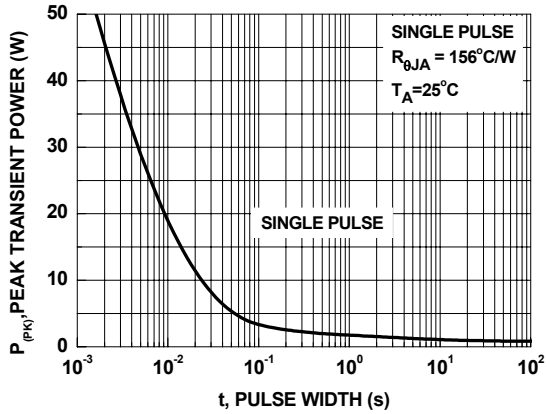


Figure 11. Single Pulse Maximum Power Dissipation

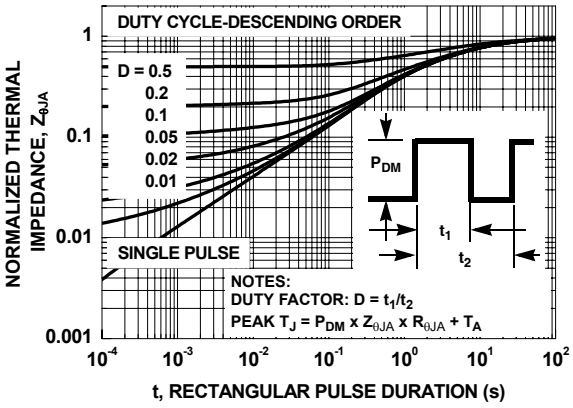


Figure 12. Transient Thermal Response Curve

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